

**NTE5962 & NTE5963
 NTE5966 & NTE5967
 Silicon Power Rectifier Diode, 25 Amp**

Features:

- 25 Amp @ $T_C = +100^\circ\text{C}$
- 300 Amp Surge Capability
- Rugged Construction
- Available in Standard (NTE5962, NTE5966) and Reverse (NTE5963, NTE5967) Polarity

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}		
NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V
Working Peak Reverse Voltage, V_{RWM}		
NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V
DC Blocking Voltage, V_B		
NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V
RMS Reverse Voltage, $V_{R(RMS)}$		
NTE5962, NTE5963*	280V
NTE5966, NTE5967*	560V
Average Rectified Forward Currnt (Single phase, resistive load, 60Hz, $T_C = +150^\circ\text{C}$), I_O	25A
Non–Repetitive Peak Surge Current (Surge applied at rated load conditions), I_{FSM}	300A
Operating Junction Temperature Range, T_J	-65° to $+175^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+175^\circ\text{C}$
Maximum Thermal Resistance, Junction–to–Case, R_{thJC}	1.2°C/W

Note 1. Standard polarity is cathode to case, (*) indicated anode to case.

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	v_F	$i_F = 57\text{A}$, $T_J = +25^\circ\text{C}$	–	–	1.7	V
Reverse Current	i_R	$V_{RRM} = \text{Rated Voltage}$, $T_C = +25^\circ\text{C}$	–	–	1.0	mA

